

**2SC3675**

900V/100mA High-Voltage Amplifier High-Voltage Switching Applications

Applications

- High voltage amplifiers.
- High-voltage switching applications.
- Dynamic focus applications.

Features

- High breakdown voltage (V_{CEO} min=900V).
- Small Cob (Cob typ=2.8pF).
- Wide ASO (Adoption of MBIT process).
- High reliability (Adoption of HVP process).

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1500	V
Collector-to-Emitter Voltage	V_{CEO}		900	V
Emitter-to-Base Voltage	V_{EBO}		5	V
Collector Current	I_C		100	mA
Collector Current (Pulse)	I_{CP}		300	mA
Collector Dissipation	P_C	$T_c=25^\circ\text{C}$	10	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=900\text{V}, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			10	μA
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}, I_C=10\text{mA}$	30			
Gain-Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}$		6		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=20\text{mA}, I_B=4\text{mA}$			5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=20\text{mA}, I_B=4\text{mA}$			2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	1500			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, R_{BE}=\infty$	900			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Output Capacitance	Cob	$V_{CB}=100\text{V}, f=1\text{MHz}$		2.8		pF

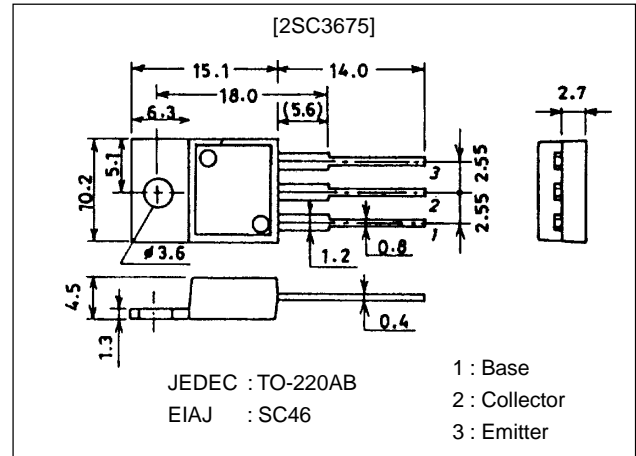
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Package Dimensions

unit:mm

2010C



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